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(54) Title of the Invention: **Through mold via polymer block package**
Abstract Title: **Through mold via polymer block package**

(57) Methods for forming an integrated circuit chip package having through mold vias in a polymer block, and such packages are described. For example, a first interconnect layer may be formed on a molded polymer block, wherein the first interconnect layer comprises first interconnects through a first polymer layer and to the block. Then, at least one second interconnect layer may be formed on the first interconnect layer, wherein the second interconnect layer comprises second interconnects through a second polymer layer and to the first interconnects of the first interconnect layer. Through mold vias may then be formed through the block, into the first interconnect layer, and to the first interconnects. The through mold vias may be filled with solder to form bumps contacting the first interconnects and extending above the block. Other embodiments are also described and claimed.

